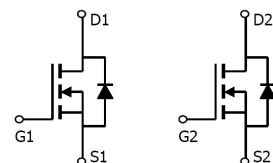


Feature

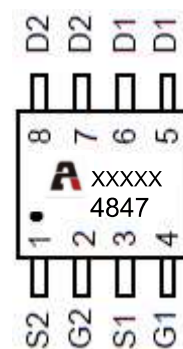
- 60V,7A
 $R_{DS(ON)} < 21m\Omega @ V_{GS}=10V$ TYP:17 m Ω
 $R_{DS(ON)} < 28m\Omega @ V_{GS}=4.5V$ TYP:22 m Ω
- Trench DMOS Power MOSFET
- Fast Switching
- Exceptional on-resistance and maximum DC current capability



Schematic diagram

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch



Marking and pin assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
4847	AP4847	SOP-8	13 inch	-	4000

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a=25^{\circ}\text{C}$)	I_D	7	A
Continuous Drain Current ($T_a=100^{\circ}\text{C}$)	I_D	5.2	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	25	A
Power Dissipation	P_D	2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	60	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =60V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽²⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.6	2.5	V
Drain-source on-resistance ⁽²⁾	R _{DS(on)}	V _{GS} =10V, I _D =7A	-	17	21	mΩ
		V _{GS} =4.5V, I _D =5A	-	22	28	
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f =1MHz	-	1115	-	pF
Output Capacitance	C _{oss}		-	91	-	
Reverse Transfer Capacitance	C _{rss}		-	82	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =30V, I _D =7A V _{GS} =10V, R _G =6Ω	-	5.9	-	ns
Turn-on rise time	t _r		-	9.1	-	
Turn-off delay time	t _{d(off)}		-	35	-	
Turn-off fall time	t _f		-	12	-	
Total Gate Charge	Q _g	V _D S=30V, I _D =7A, V _G S=10V	-	27	-	nC
Gate-Source Charge	Q _{gs}		-	2.9	-	
Gate-Drain Charge	Q _{gd}		-	7.6	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽²⁾	V _{DS}	V _{GS} =0V, I _S =57	-	-	1.2	V
Diode Forward current ⁽³⁾	I _S		-	-	7	A
Reverse recovery time	T _{rr}	I _S =7A,V _{GS} =0V,dI _F /dt=100A/us		27		ns
Reverse recovery charge	Q _{rr}	I _S =7A,V _{GS} =0V,dI _F /dt=100A/us		23		nC

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. Surface Mounted on FR4 Board, $t \leq 10$ sec

Typical Characteristics (@ $T_J = 25^\circ\text{C}$, unless otherwise specified.)

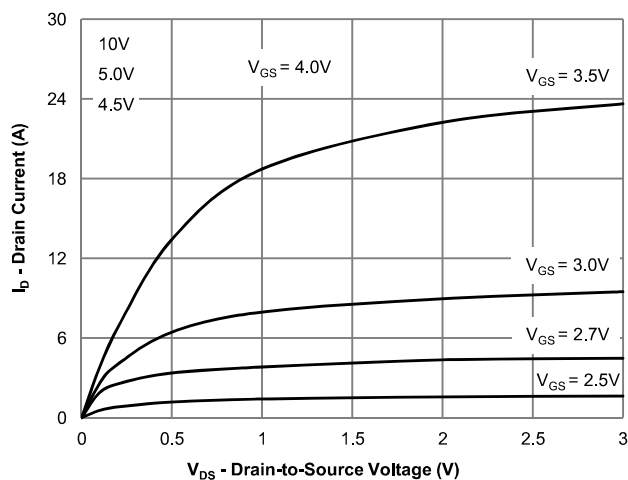


Figure 1: Output Characteristics

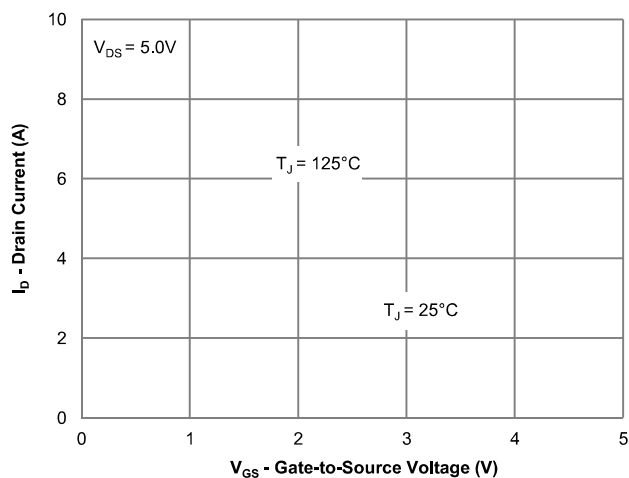


Figure 2: Transfer Characteristics

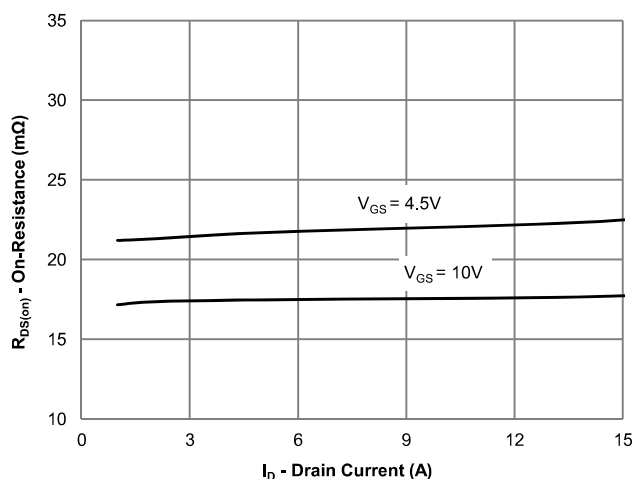


Figure 3: On-Resistance vs. Gate-Source Voltage

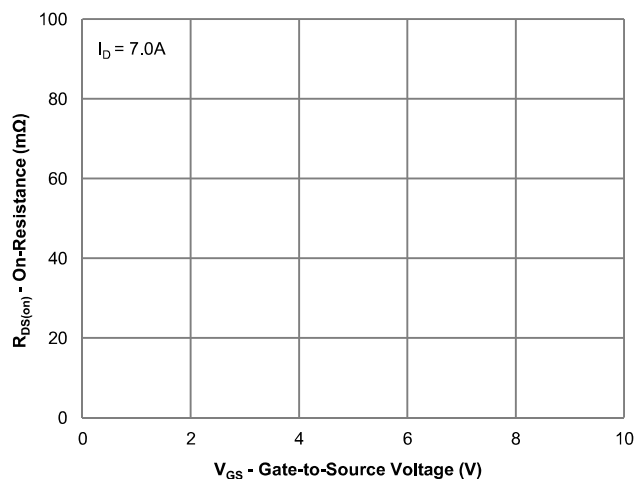


Figure 4: On-Resistance vs. Gate-Source Voltage

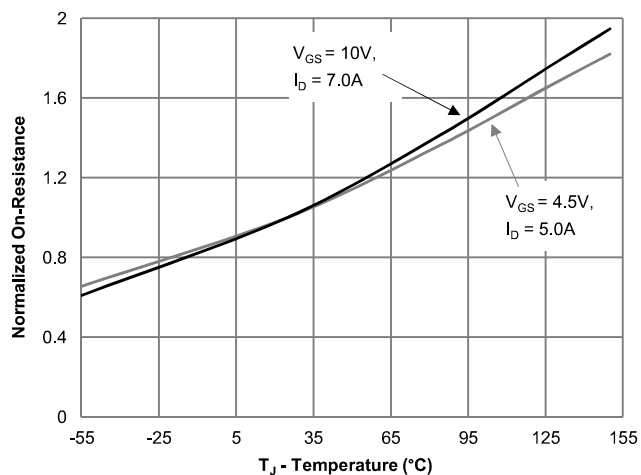


Figure 5: On-Resistance vs. Junction Temperature

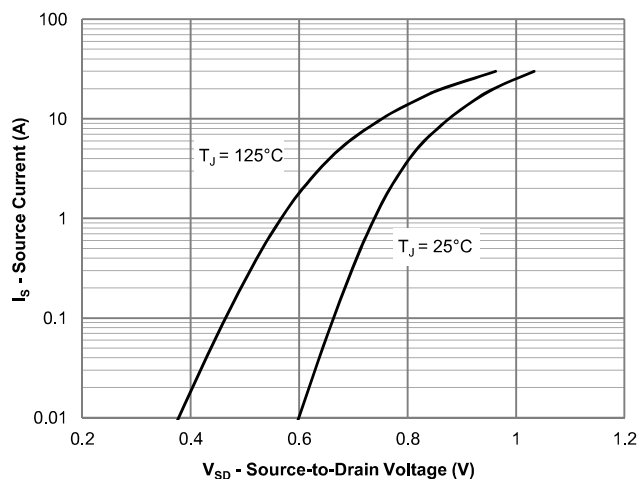


Figure 6: Source-Drain Diode Forward Voltage

Typical Characteristics (@ $T_J = 25^\circ\text{C}$, unless otherwise specified.)

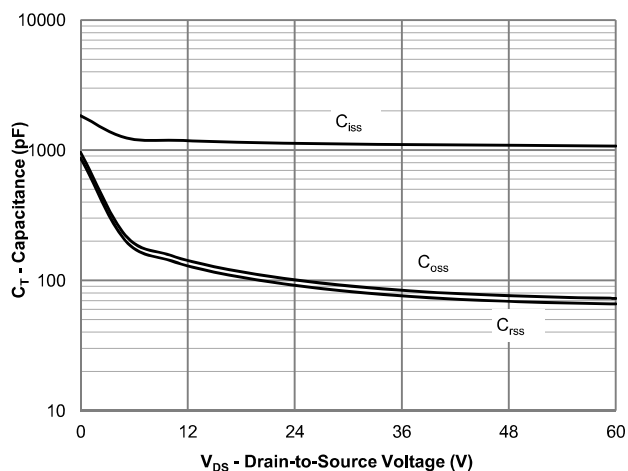


Figure 7: Capacitance Characteristics

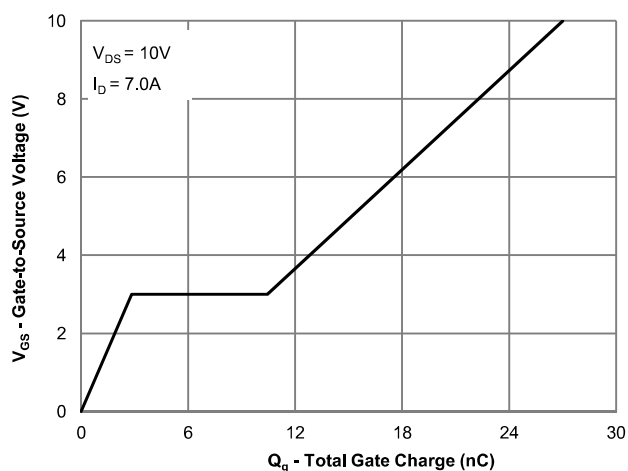


Figure 8: Gate Charge Characteristics

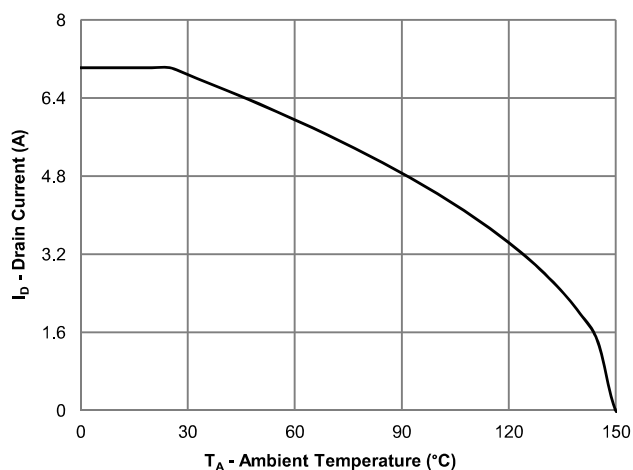


Figure 9: Current Derating

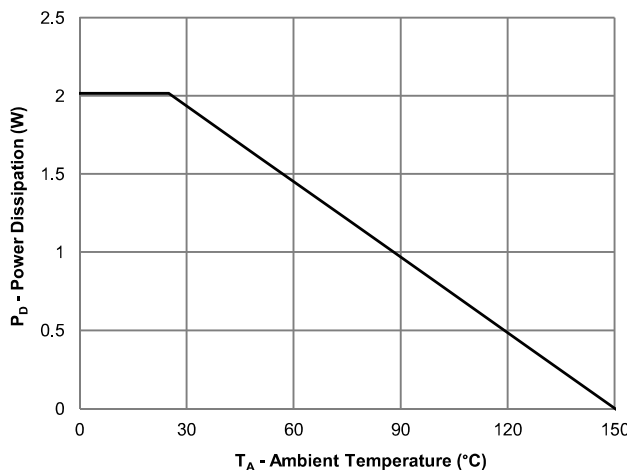


Figure 10: Power Derating

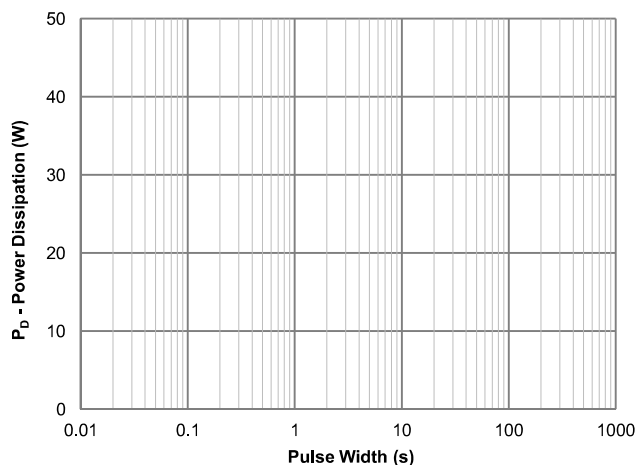


Figure 11: Single Pulse Power, Junction-to-Ambient

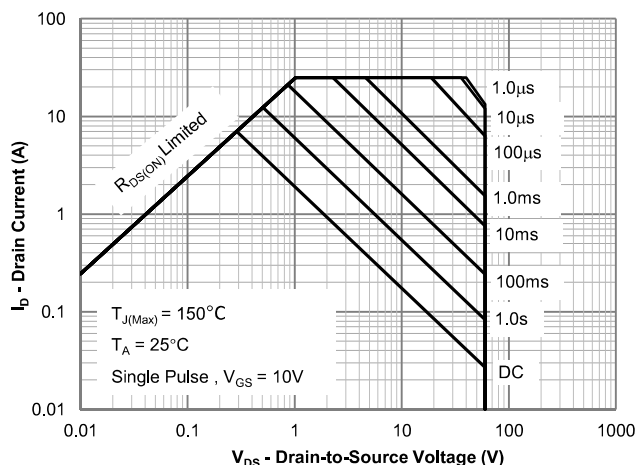


Figure 12: Safe Operating Area

Typical Characteristics (@ $T_J = 25^{\circ}\text{C}$, unless otherwise specified.)

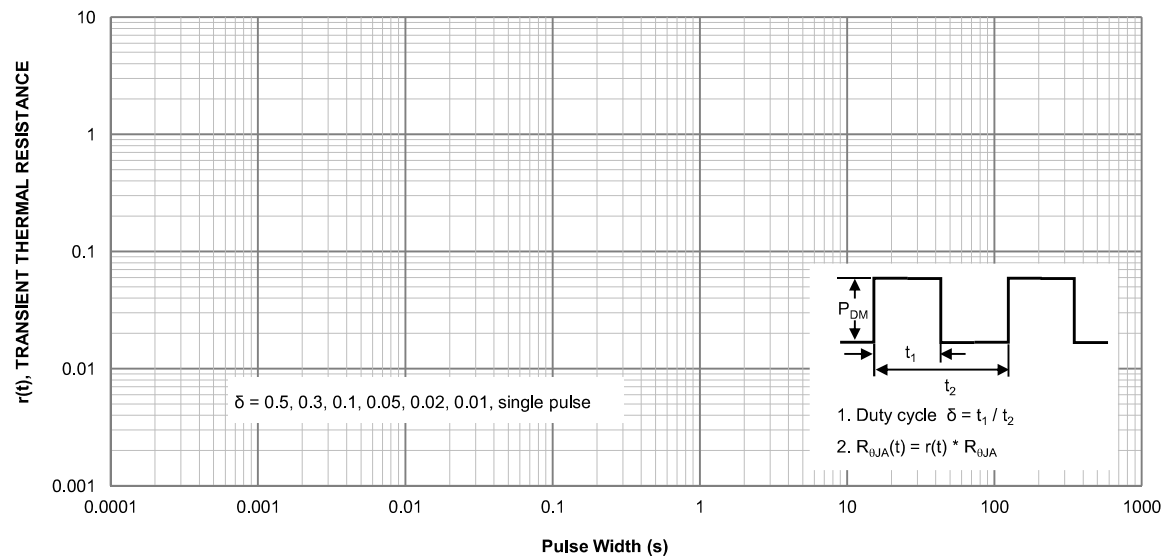
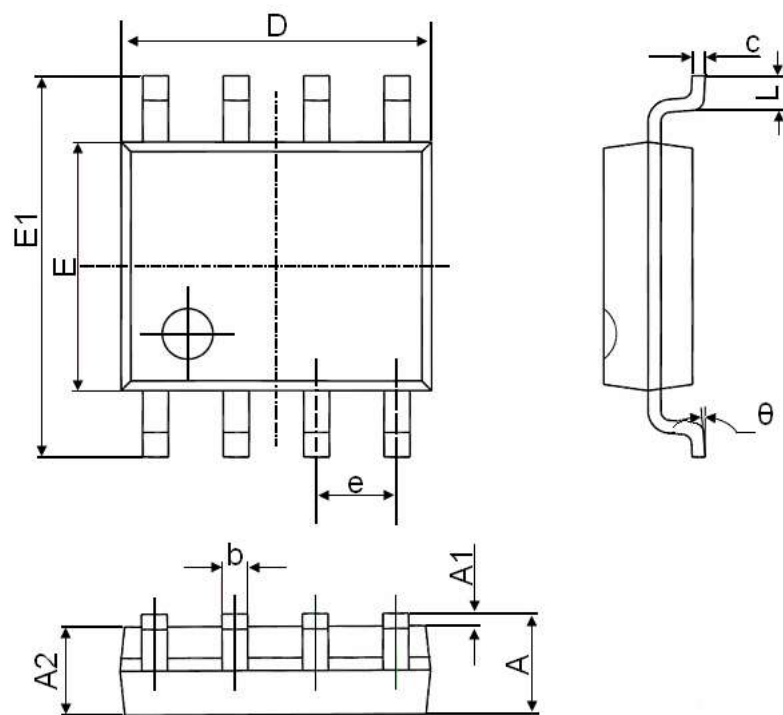


Figure 13: Normalized Thermal Transient Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°